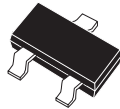


CMPF4416A
SILICON N-CHANNEL JFET



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPF4416A type is an epoxy molded N-Channel Silicon Junction Field Effect Transistor manufactured in an SOT-23 case, designed for VHF amplifier and mixer applications.

Marking code is 6BG.

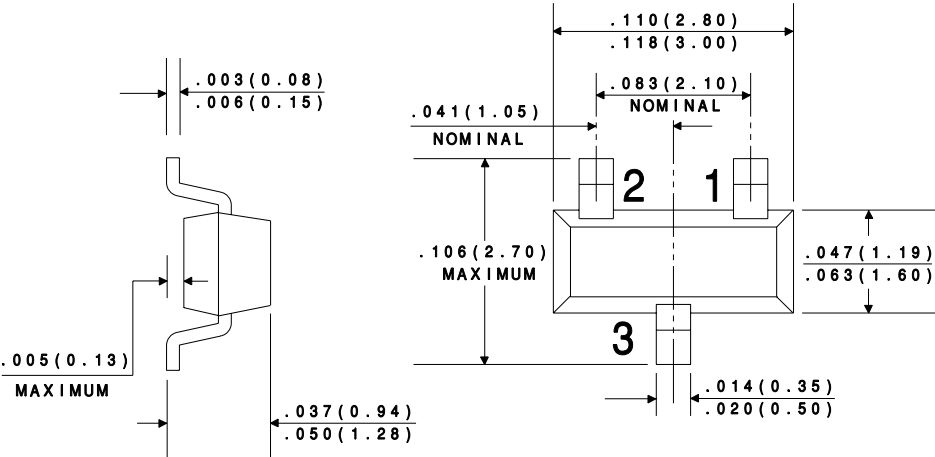
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Drain-Source Voltage	V_{DS}	35	V
Gate-Source Voltage	V_{GS}	35	V
Gate Current	I_G	10	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	357	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{GSS}	$V_{GS}=20\text{V}$		1.0	nA
I_{DSS}	$V_{DS}=15\text{V}, V_{GS}=0$	5.0	15	mA
BV_{GSS}	$I_G=1.0\mu\text{A}$	35		V
$V_{GS(off)}$	$V_{DS}=15\text{V}, I_D=1.0\text{nA}$	2.5	6.0	V
g_{fs}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{kHz}$	4.5	7.5	mmhos
C_{iss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		4.5	pF
C_{rss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		1.2	pF
N_F	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{kHz}, R_G=1.0\text{M}\Omega$		2.5	dB

All dimensions in inches (mm).



LEAD CODE:

- 1) DRAIN
- 2) SOURCE
- 3) GATE